TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS060

CD4085B Types

CMOS Dual 2-Wide 2-Input AND-OR-INVERT Gate

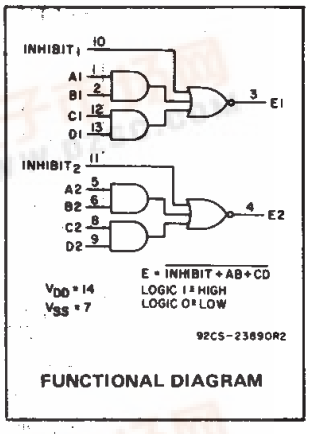
High-Voltage Types (20-Volt Rating)

■ CD4085 contains a pair of AND-OR-INVERT gates, each consisting of two 2-input AND gates driving a 3-input NOR gate. Individual inhibit controls are provided for both A-O-I gates.

The CD4085B types are supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- Medium-speed operation — t_{PHL} = 90 ns; t_{PLH} = 125 ns (typ.) at 10 V
- Individual inhibit controls
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package-temperature range):
  - 1 V at V_{DD} = 5 V
  - 2 V at V_{DD} = 10 V
  - 2.5 V at V_{DD} = 15 V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



FUNCTIONAL DIAGRAM

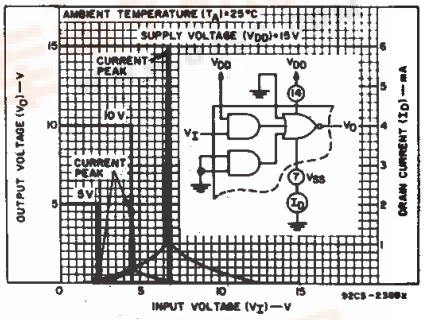


Fig. 1 — Typical voltage and current transfer characteristics.

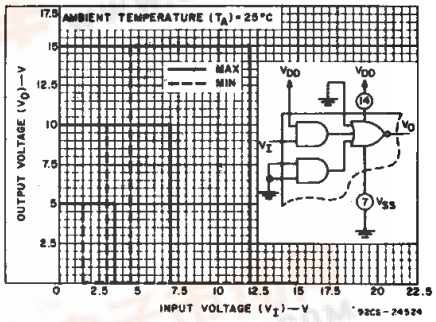


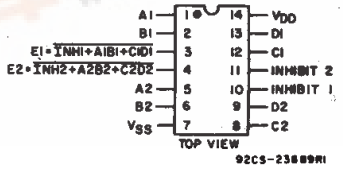
Fig. 2 — Min. and max. voltage transfer characteristics.

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

RECOMMENDED OPERATING CONDITIONS
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For T_A = Full Package-Temperature Range)	3	18	V



Terminal Assignment

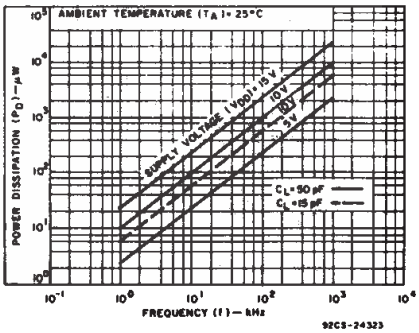


Fig. 3 — Typical power dissipation vs. frequency.

3 COMMERCIAL CMOS HIGH VOLTAGE ICs

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	+25 Min.	+25 Typ.	+25 Max.	
Quiescent Device Current I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current, I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5,4.5	–	5	1.5				–	–	1.5	V
	1,9	–	10	3				–	–	3	
	1.5,13.5	–	15	4				–	–	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	–	–	
	1,9	–	10	7				7	–	–	
	1.5,13.5	–	15	11				11	–	–	
Input Current, I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

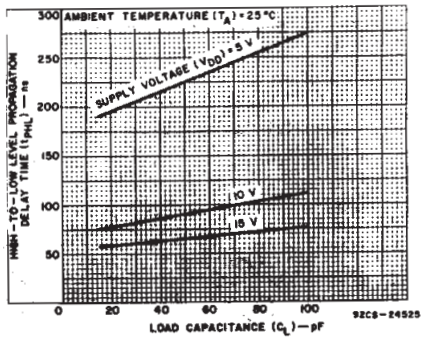


Fig. 4 – Typical data high-to-low level propagation delay time vs. load capacitance.

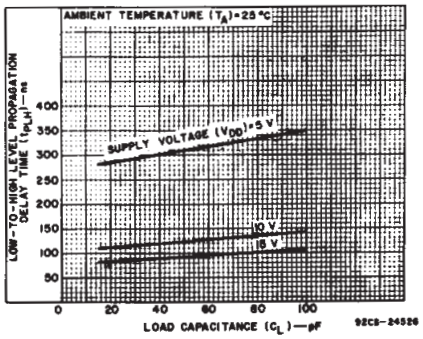


Fig. 5 – Typical data low-to-high level propagation delay time vs. load capacitance.

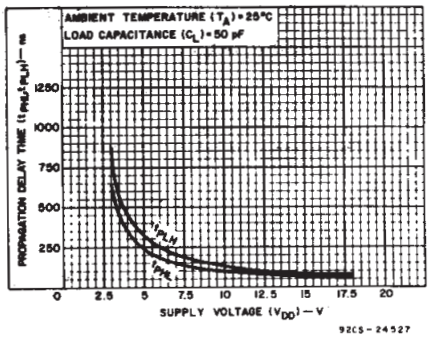


Fig. 6 – Typical data propagation delay time vs. supply voltage.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 KΩ

CHARACTERISTIC		CONDITIONS V_{DD} V	LIMITS Typ.	LIMITS Max.	UNITS
Propagation Delay Time (Data): High-to-Low Level,	t_{PHL}	5	225	450	ns
		10	90	180	
		15	65	130	
Low-to-High Level,	t_{PLH}	5	310	620	ns
		10	125	250	
		15	90	180	
Propagation Delay Time (Inhibit): High-to-Low Level,	t_{PHL}	5	150	300	ns
		10	60	120	
		15	40	80	
Low-to-High Level,	t_{PLH}	5	250	500	ns
		10	100	200	
		15	70	140	
Transition Time,	t_{THL}, t_{TLH}	5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance,	C_{IN}	Any Input	5	7.5	pF

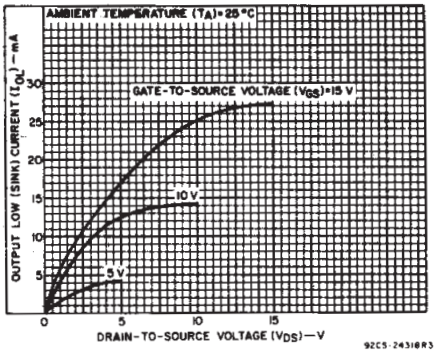


Fig. 7 — Typical output low (sink) current characteristics.

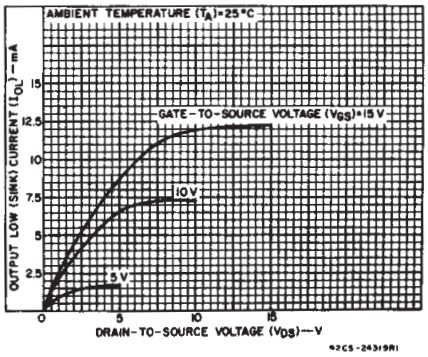


Fig. 8 — Minimum output low (sink) current characteristics.

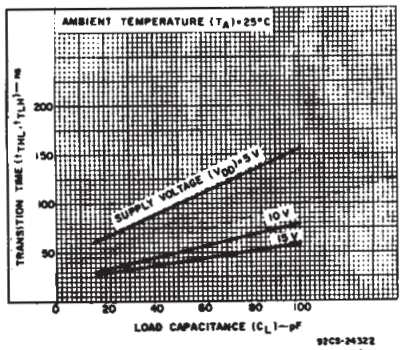


Fig. 9 — Typical transition time vs. load capacitance.

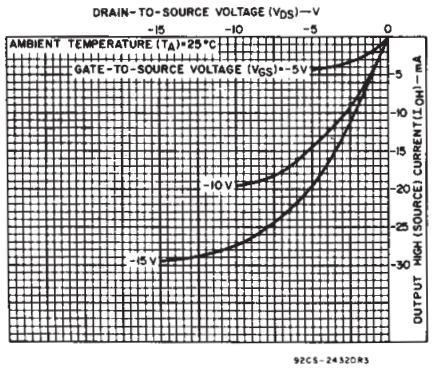


Fig. 10 — Typical output high (source) current characteristics.

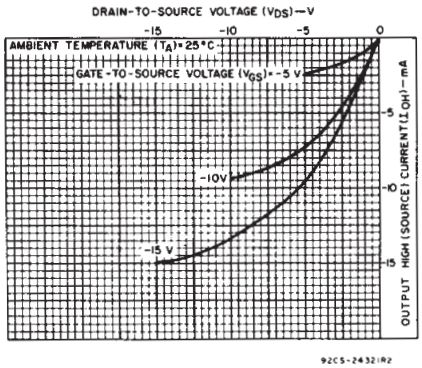


Fig. 11 — Minimum output high (source) current characteristics.

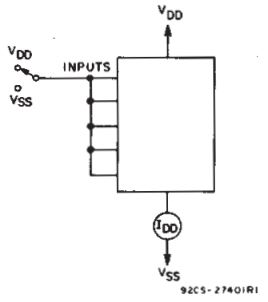


Fig. 12 — Quiescent device current test circuit.

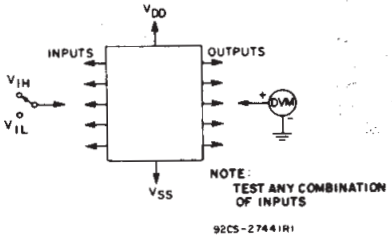


Fig. 13 — Input voltage test circuit.

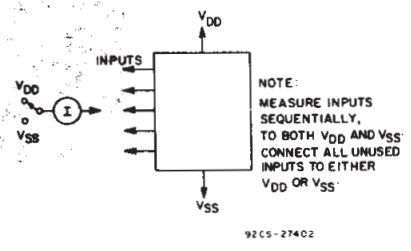


Fig. 14 — Input current test circuit.

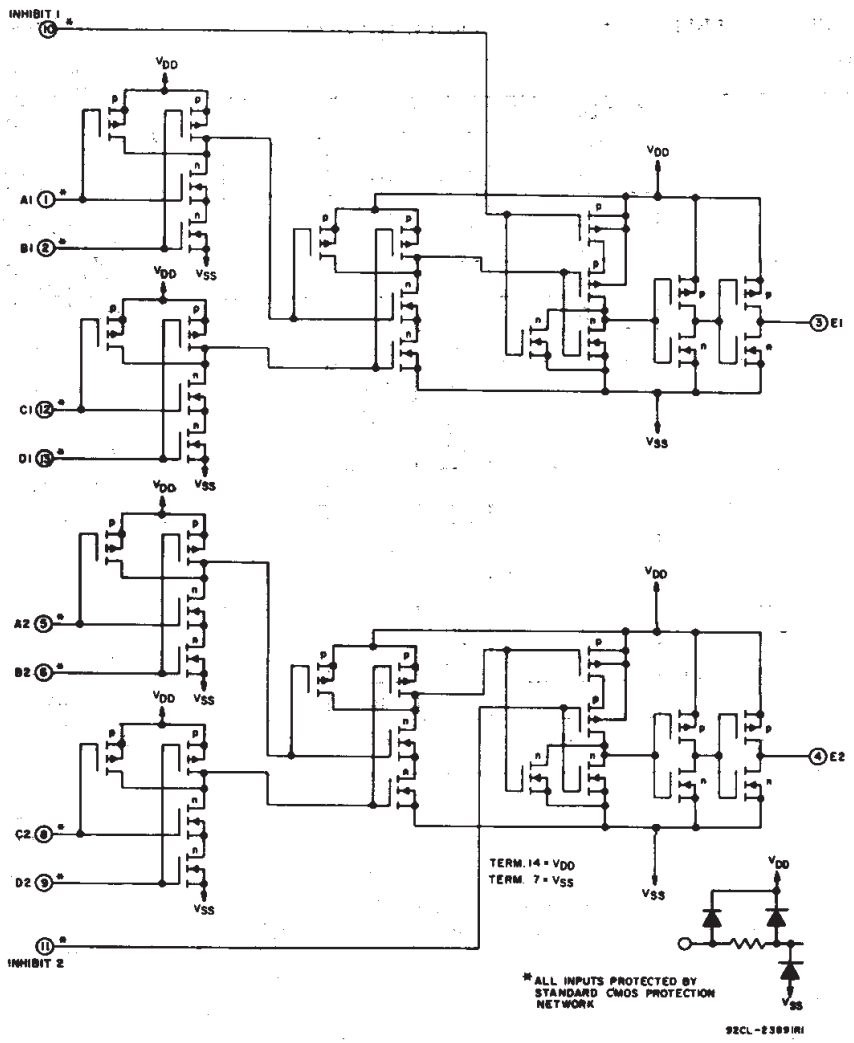
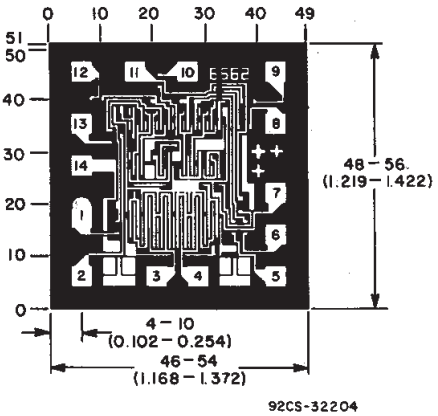


Fig. 15 – CD4085 schematic diagram.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and Pad Layout for CD4085BH.

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